

Japanese Unexamined Patent Publication No. 49(1974)-131646

Publication Date: December 17, 1974

Japanese Classification: 97(7)C5, 97(7)C19

Application No.: JP48(1973)-45549

5 Application Date: April 20, 1973

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Title of the Invention:

10 Storage Element Specialized in Readout

Claim:

15 A storage element for readout, comprising an ohmic electrode provided on a single-crystal silicon substrate, wherein two dependent areas each of which has a conduction type different from that of the crystal of the substrate are provided in the single-crystal silicon substrate so that they are sufficiently close to each other, and wherein metal electrodes are attached to the two areas so as to form a source electrode and a drain electrode, respectively, and wherein a layer made of silicon oxide is formed on the
20 single-crystal silicon substrate between the source electrode and the drain electrode, and wherein a metal is attached onto the layer to form a floating gate electrode, and wherein a ferroelectric is further attached onto the floating gate electrode, and wherein a metal electrode is further attached onto the ferroelectric layer so as to form a gate electrode,.